











SN74LVC2G07

SCES308L-AUGUST 2001-REVISED MAY 2015

# SN74LVC2G07 Dual Buffer and Driver With Open-Drain Outputs

#### **Features**

- **Dual Open-Drain Buffer Configuration**
- -24-mA Output Drive at 3.3 V
- Support Translation-Up and Down
- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V<sub>CC</sub> Operation
- Inputs and Open-Drain Outputs Accept Voltages Up to 5.5 V
- Max  $t_{pd}$  of 3.7 ns at 3.3 V
- Low Power Consumption, 10-µA Max I<sub>CC</sub>
- Typical V<sub>OLP</sub> (Output Ground Bounce)  $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot) >2 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- Ioff Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

#### 2 Applications

- Blu-ray Players and Home Theaters
- **DVD Recorders and Players**
- Desktops or Notebook PCs
- Digital Video Cameras (DVC)
- Embedded PCs
- **GPS: Personal Navigation Devices**
- Mobile Phones
- **Network Projector Front Ends**
- Portable Media Players
- Solid State Drive (SSD): Enterprise
- High-Definition (HDTV)
- Tablet: Enterprise
- Audio Dock: Portable
- **DLP Front Projection System**

## 3 Description

This dual buffer and driver is designed for 1.65-V to The output operation. of the SN74LVC2G07 device is open drain and can be connected to other open-drain outputs to implement active-low wired-OR or active-high wired-AND functions. The maximum sink current is 32 mA.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

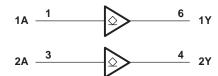
This device is fully specified for partial-power-down applications using  $I_{\text{off}}$ . The  $I_{\text{off}}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

## Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	SOT-23 (6)	2.90 mm × 1.60 mm
	SC70 (6)	2.00 mm × 1.25 mm
SN74LVC2G07	DRY SON (6)	1.45 mm × 1.00 mm
	DSF SON (6)	1.00 mm × 1.00 mm
	DSBGA (6)	1.41 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

## **Functional Block Diagram**





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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

#### Changes from Revision K (November 2013) to Revision L

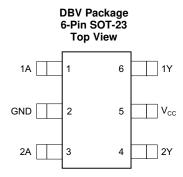
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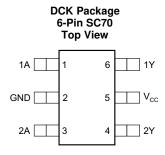
#### Changes from Revision J (August 2012) to Revision K

**Page** 



# 5 Pin Configuration and Functions

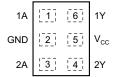




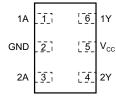




#### DRY Package 6-Pin SON Top View



#### DSF Package 6-Pin SON Top View



## **Pin Functions**

Р	IN	I/O	DESCRIPTION
NAME	E NO		DESCRIPTION
1A	1	I	Input 1
GND	2	_	Ground
2A	3	I	Input 2
2Y	4	0	Open-drain output 2
V <sub>CC</sub>	5	_	Power pin
1Y	6	I	Open-drain output 1



# 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	I MAX	UNIT
$V_{CC}$	Supply voltage		-0.8	6.5	V
VI	Input voltage (2)		-0.5	6.5	V
Vo	Voltage applied to any output in the high-impedance or power-off state (2)		-0.5	6.5	V
Vo	Voltage applied to any output in the high or low state (2)(3)		-0.5	6.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		<b>–</b> 50	mA
Io	Continuous output current			±50	mA
	Continuous current through V <sub>CC</sub> or GND			±100	mA
T <sub>stg</sub>	Storage Temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	+2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	+1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions(1)

			MIN	MAX	UNIT
V	Cupply voltage	Operating	1.65	5.5	V
V <sub>CC</sub>	Supply voltage	Data retention only	1.5		V
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		
V	High lovel input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
V <sub>IH</sub>	High-level input voltage	$V_{CC} = 3 V \text{ to } 3.6 V$	2		V
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	
V	Low level input valtage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
$V_{IL}$	Low-level input voltage	$V_{CC} = 3 V \text{ to } 3.6 V$		0.8	V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$	
$V_{I}$	Input voltage	·	0	5.5	V
$V_{O}$	Output voltage		0	5.5	V
		V <sub>CC</sub> = 1.65 V		4	
		V <sub>CC</sub> = 2.3 V		8	
I <sub>OL</sub>	Low-level output current	V 2 V		16	mA
		V <sub>CC</sub> = 3 V		24	
		V <sub>CC</sub> = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		ns/V	
		V <sub>CC</sub> = 5 V ± 0.5 V		5	

<sup>(1)</sup> All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

<sup>(2)</sup> The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(3)</sup> The value of  $V_{CC}$  is provided in the *Recommended Operating Conditions* table.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



# Recommended Operating Conditions<sup>(1)</sup> (continued)

		MIN	MAX	UNIT
$T_A$	Operating free-air temperature	-40	125	°C

#### 6.4 Thermal Information

				SN74LVC2G07			
	THERMAL METRIC <sup>(1)</sup>	SOT-23	SC70	DRY (SON)	DSBGA	DSF (SON)	UNIT
		6 PINS	6 PINS	6 PINS	6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	165	259	234	123	300	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

#### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST COMPLICATE	v	–40°C to 85°C	–40°C to 125°C	UNIT
PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN TYP <sup>(1)</sup> MAX	MIN TYP <sup>(1)</sup> MAX	UNII
	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V	0.1	0.1	
	I <sub>OL</sub> = 4 mA	1.65 V	0.45	0.45	
W	I <sub>OL</sub> = 8 mA	2.3 V	0.3	0.3	V
V <sub>OL</sub>	I <sub>OL</sub> = 16 mA	3 V	0.4	0.4	
	I <sub>OL</sub> = 24 mA	3 V	0.55	0.55	
	I <sub>OL</sub> = 32 mA	4.5 V	0.55	0.55	
I <sub>I</sub> A inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V	±5	±5	μΑ
I <sub>off</sub>	$V_1$ or $V_0 = 5.5 \text{ V}$	0	±10	±10	μΑ
I <sub>CC</sub>	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V	10	10	μΑ
ΔI <sub>CC</sub>	One input at $V_{CC}$ – 0.6 V, Other inputs at $V_{CC}$ or GND	3 V to 5.5 V	500	500	μΑ
Cı	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V	3.5	3.5	pF

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.

## 6.6 Switching Characteristics from -40°C to 85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

						-40°C	to 85°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1 ± 0.15		V <sub>CC</sub> = 2 ± 0.2		V <sub>CC</sub> = 3 ± 0.3		V <sub>CC</sub> = ± 0.5		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	Α	Υ	1.5	8.6	1	4.4	1	3.7	1	2.9	ns

## 6.7 Switching Characteristics from -40°C to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

						–40°C to	125°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1 ± 0.15		V <sub>CC</sub> = 2 ± 0.2		V <sub>CC</sub> = 3 ± 0.3		V <sub>CC</sub> = ± 0.5		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	Α	Υ	1.5	8.6	1	4.9	1	4.2	1	3.4	ns

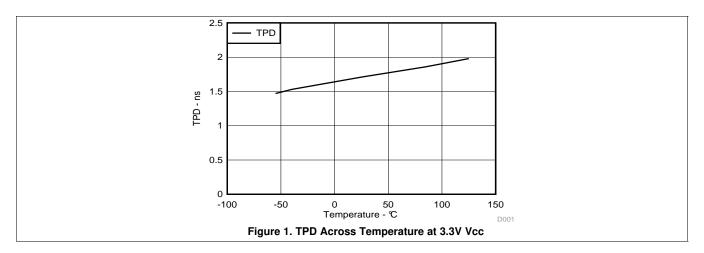
## 6.8 Operating Characteristics

 $T_A = 25^{\circ}C$ 

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT
	FARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	ONIT
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	3	3	4	4	pF



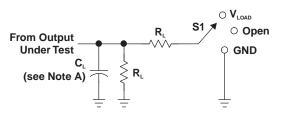
# 6.9 Typical Characteristics





#### 7 Parameter Measurement Information

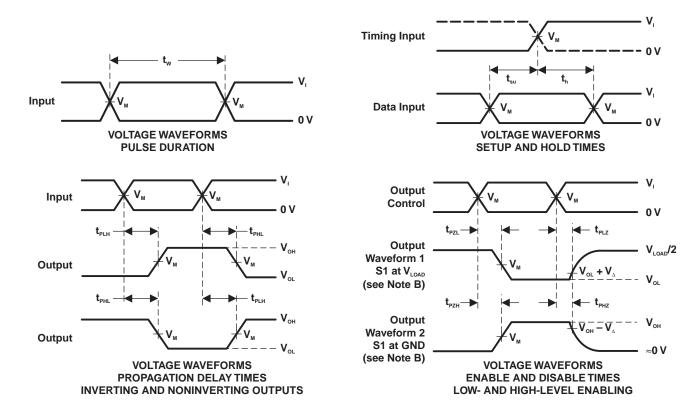
#### 7.1 (Open-Drain)



TEST	S1
t <sub>PZL</sub> (see Notes E and F)	<b>V</b> <sub>LOAD</sub>
t <sub>PLZ</sub> (see Notes E and G)	$V_{\scriptscriptstyle LOAD}$
t <sub>PHZ</sub> /t <sub>PZH</sub>	$\mathbf{V}_{LOAD}$

LOAD CIRCUIT
--------------

.,	INI	PUTS	.,	v		_	.,
V <sub>cc</sub>	V,	t,/t,	V <sub>M</sub>	V <sub>LOAD</sub>	C <sub>∟</sub>	R <sub>∟</sub>	V <sub>Δ</sub>
$1.8~\textrm{V}\pm0.15~\textrm{V}$	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	<b>1 k</b> Ω	0.15 V
2.5 V $\pm$ 0.2 V	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	500 Ω	0.15 V
3.3 V $\pm$ 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V $\pm$ 0.5 V	V <sub>cc</sub>	≤2.5 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	50 pF	<b>500</b> Ω	0.3 V



NOTES: A. C. includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators have the following characteristics: PRR  $\leq$  10 MHz,  $Z_0 = 50 \Omega$ .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. Because this device has open-drain outputs,  $t_{\mbox{\tiny PLZ}}$  and  $t_{\mbox{\tiny PZL}}$  are the same as  $t_{\mbox{\tiny PD}}$ .
- F.  $t_{\tiny PZL}$  is measured at  $V_{\tiny M}$ .
- G.  $t_{PLZ}$  is measured at  $V_{OL} + V_{\Delta}$ .
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

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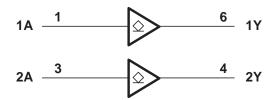


## 8 Detailed Description

#### 8.1 Overview

The SN74LVC2G07 device contains two open drain buffer with a maximum sink current of 32 mA. This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

#### 8.2 Functional Block Diagram



## 8.3 Feature Description

The open-drain configuration means that the device cannot provide its own output drive current; instead, it relies on pullup resistors to provide the "high" bus state. It can only drive the bus low. In the "Hi-Z" state, the SN74LVC2G07 acts as an open circuit and allows the external pullup to pull the bus high. Therefore, the pullup voltage determines the output level and therefore the SN74LVC2g07 can be used for up or down-translation. The device can sink 24 mA at 3 V while retaining an output voltage (V<sub>OI</sub>) of 0.55 V or lower.

#### 8.4 Device Functional Modes

Table 1 shows the device functional modes of the SN74LVC2G07 device.

**Table 1. Function Table** 

INPUT A	OUTPUT Y
L	L
Н	Н



# 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

The SN74LVC2G07 is a high-drive CMOS device that can be used to implement a high output drive buffer, such as an LED application. It can sink 32 mA of current at 4.5 V making it ideal for high-drive and wired-OR/AND functions. The inputs are 5.5 V tolerant allowing it to translate up and down to  $V_{CC}$ .

## 9.2 Typical Application

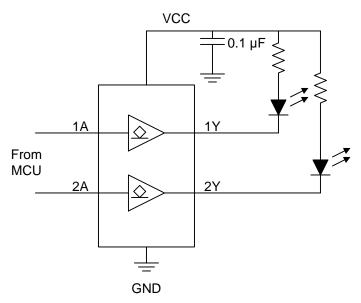


Figure 3. Typical Application

#### 9.2.1 Design Requirements

- 1. Recommended Input Conditions
  - Rise time and fall time specs. See (Δt/ΔV) in the Recommended Operating Conditions table.
  - Specified high and low levels. See (V<sub>IH</sub> and V<sub>IL</sub>) in the Recommended Operating Conditions table.
  - Inputs are overvoltage tolerant allowing them to go as high as (V<sub>I</sub> max) in the Recommended Operating
     Conditions table at any valid V<sub>CC</sub>.

#### 2. Recommend Output Conditions

- Load currents should not exceed ( $I_O$  max) per output and should not exceed (Continuous current through  $V_{CC}$  or GND) total current for the part. These limits are located in the *Absolute Maximum Ratings* table.
- Outputs should not be pulled above 5.5 V.

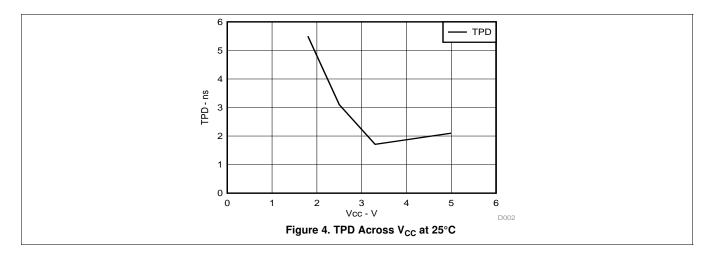
#### 9.2.2 Detailed Design Procedure

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.



## **Typical Application (continued)**

#### 9.2.3 Application Curve



# 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions* table.

Each  $V_{CC}$  pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply a 0.1- $\mu$ F capacitor is recommended and if there are multiple  $V_{CC}$  pins then a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

## 11 Layout

#### 11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$  whichever make more sense or is more convenient.

#### 11.2 Layout Examples



Figure 5. Layout Examples for SN74LVC2G07

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## 12 Device and Documentation Support

## 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation, see the following: Implications of Slow or Floating CMOS Inputs, SCBA004.

#### 12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.3 Trademarks

NanoFree, E2E are trademarks of Texas Instruments.

#### 12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





25-Oct-2016

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN74LVC2G07DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-40 to 125	(C075 ~ C07F ~ C07K ~ C07R)	Samples
SN74LVC2G07DBVRE4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C07F	Samples
SN74LVC2G07DBVRG4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C07F	Samples
SN74LVC2G07DCKR	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CV5 ~ CVF ~ CVK ~ CVR)	Samples
SN74LVC2G07DCKRE4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CV5 ~ CVF ~ CVK ~ CVR)	Samples
SN74LVC2G07DCKRG4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CV5 ~ CVF ~ CVK ~ CVR)	Samples
SN74LVC2G07DCKT	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CV5 ~ CVF ~ CVK ~ CVR)	Samples
SN74LVC2G07DCKTG4	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CV5 ~ CVF ~ CVK ~ CVR)	Samples
SN74LVC2G07DRYR	ACTIVE	SON	DRY	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CV	Samples
SN74LVC2G07DSFR	ACTIVE	SON	DSF	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CV	Samples
SN74LVC2G07YEPR	OBSOLETE	DSBGA	YEP	6		TBD	Call TI	Call TI	-40 to 125		
SN74LVC2G07YZPR	ACTIVE	DSBGA	YZP	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	(CV7 ~ CVN)	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



## PACKAGE OPTION ADDENDUM

25-Oct-2016

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN74LVC2G07:

■ Enhanced Product: SN74LVC2G07-EP

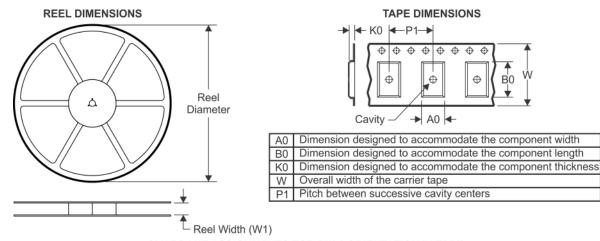
NOTE: Qualified Version Definitions:

• Enhanced Product - Supports Defense, Aerospace and Medical Applications

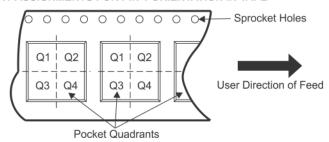
# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION



## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

All difficults are norminal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G07DBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G07DBVRG4	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G07DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC2G07DCKR	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G07DCKT	SC70	DCK	6	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G07DCKT	SC70	DCK	6	250	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
SN74LVC2G07DCKT	SC70	DCK	6	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC2G07DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC2G07DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC2G07YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

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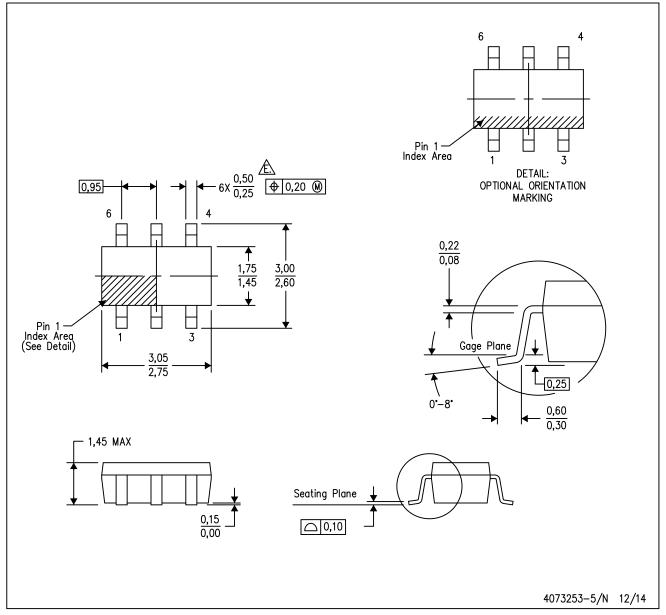


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G07DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
SN74LVC2G07DBVRG4	SOT-23	DBV	6	3000	180.0	180.0	18.0
SN74LVC2G07DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G07DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G07DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC2G07DCKT	SC70	DCK	6	250	205.0	200.0	33.0
SN74LVC2G07DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC2G07DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC2G07DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC2G07YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0

DBV (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



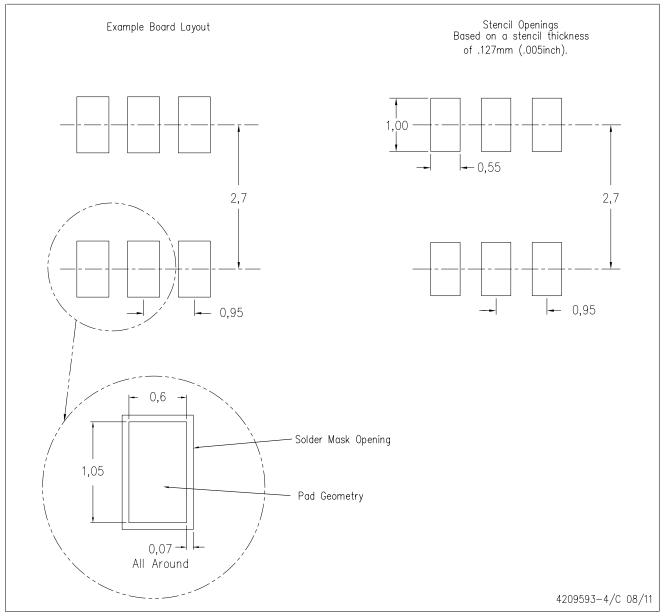
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



# DBV (R-PDSO-G6)

# PLASTIC SMALL OUTLINE



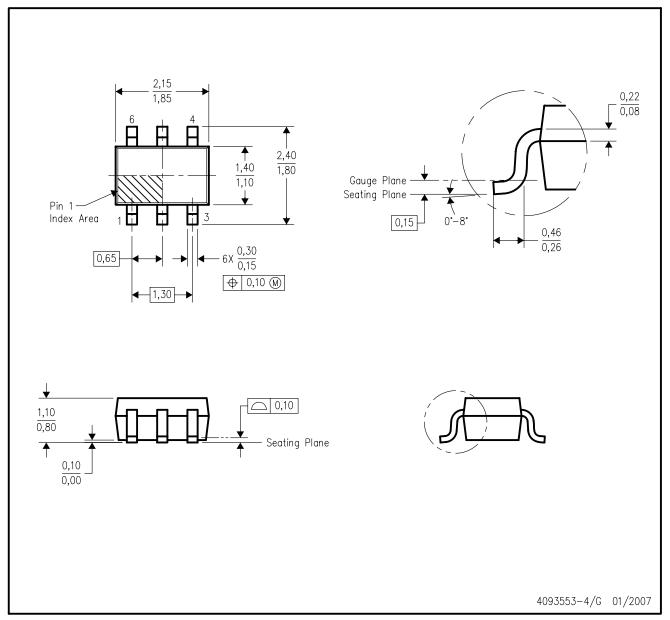
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



# DCK (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



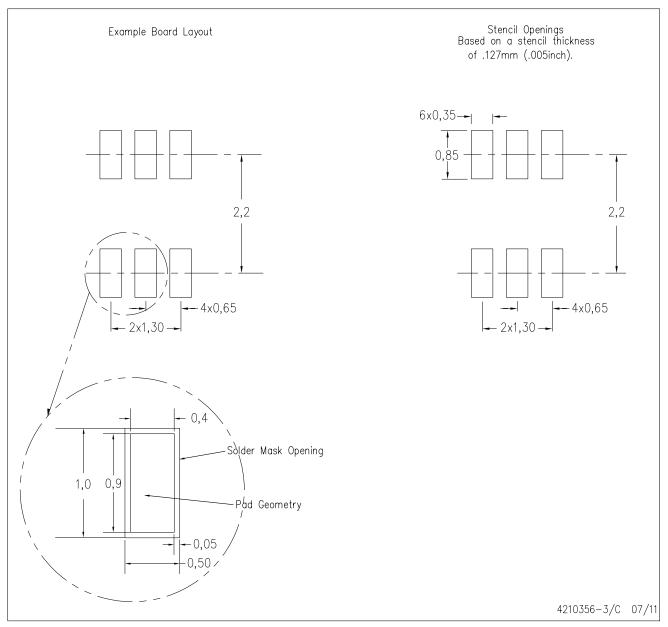
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



# DCK (R-PDSO-G6)

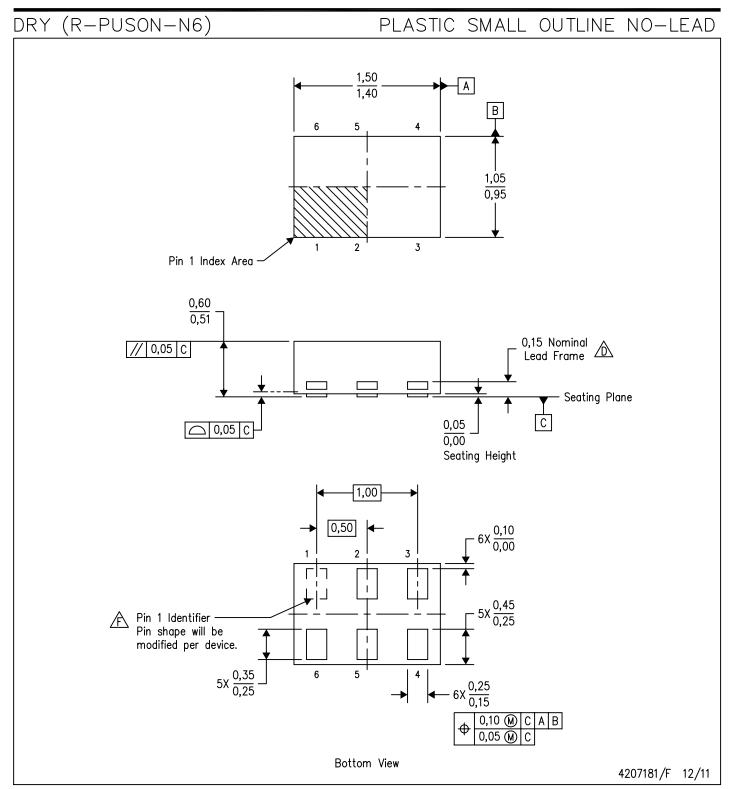
# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. SON (Small Outline No-Lead) package configuration.

The exposed lead frame feature on side of package may or may not be present due to alternative lead frame designs.

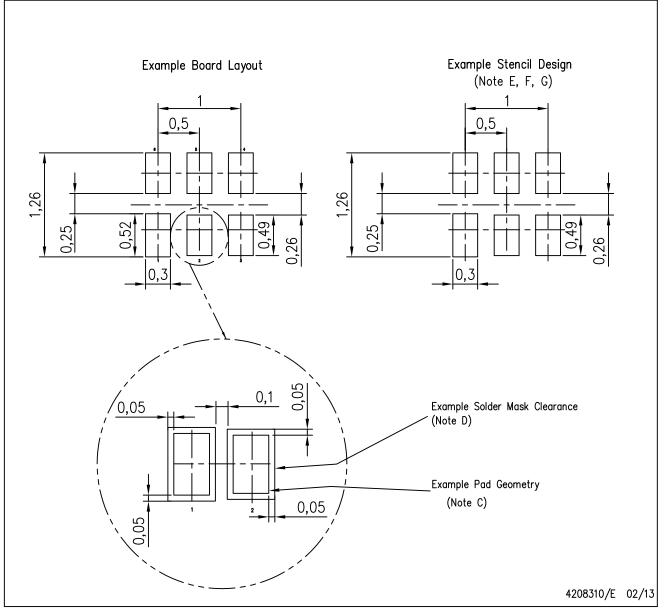
E. This package complies to JEDEC MO-287 variation UFAD.

 $frac{f}{K}$  See the additional figure in the Product Data Sheet for details regarding the pin 1 identifier shape.



# DRY (R-PUSON-N6)

## PLASTIC SMALL OUTLINE NO-LEAD



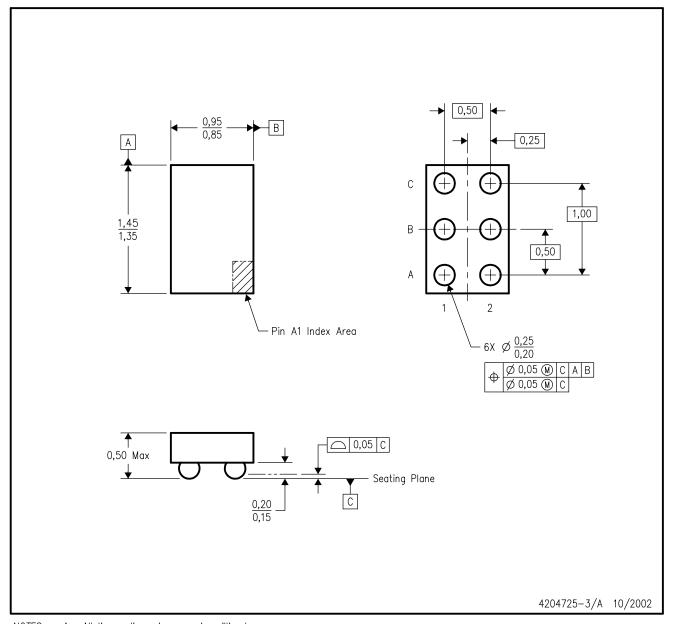
NOTES: A.

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
- E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Side aperture dimensions over—print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



# YEP (R-XBGA-N6)

# DIE-SIZE BALL GRID ARRAY

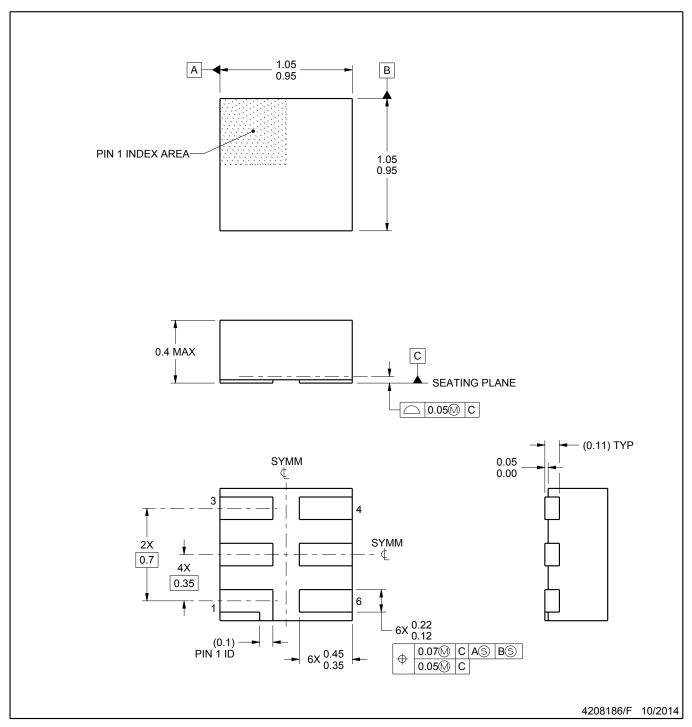


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar  $\mathbf{M}$  package configuration.
- D. This package is tin-lead (SnPb). Refer to the 6 YZP package (drawing 4204741) for lead-free.

NanoStar is a trademark of Texas Instruments.





#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

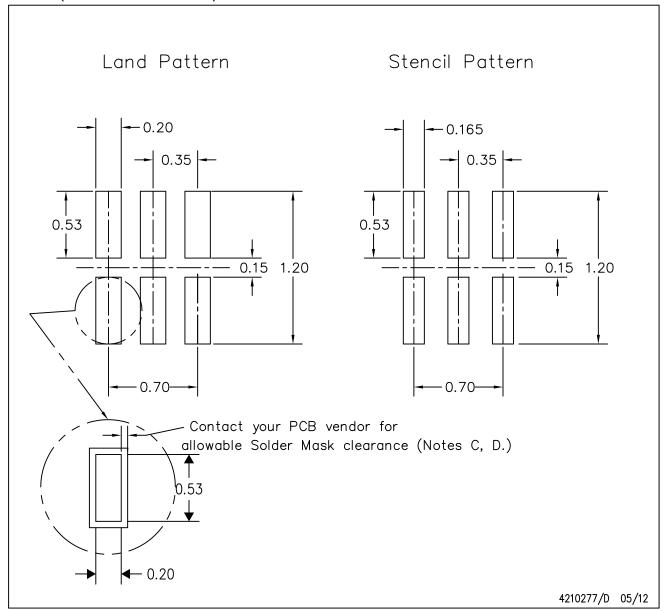
  2. This drawing is subject to change without notice.

  3. Reference JEDEC registration MO-287, variation X2AAF.



DSF (S-PX2SON-N6)

PLASTIC SMALL OUTLINE NO-LEAD



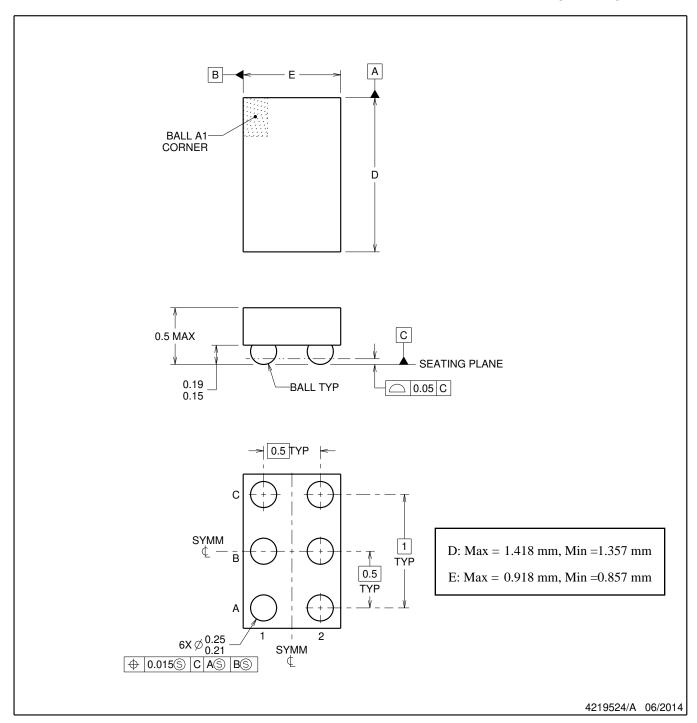
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads. If 2 mil solder mask is outside PCB vendor capability, it is advised to omit solder mask.
- E. Maximum stencil thickness 0,1016 mm (4 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Suggest stencils cut with lasers such as Fiber Laser that produce the greatest positional accuracy.
- H. Component placement force should be minimized to prevent excessive paste block deformation.





DIE SIZE BALL GRID ARRAY



#### NOTES:

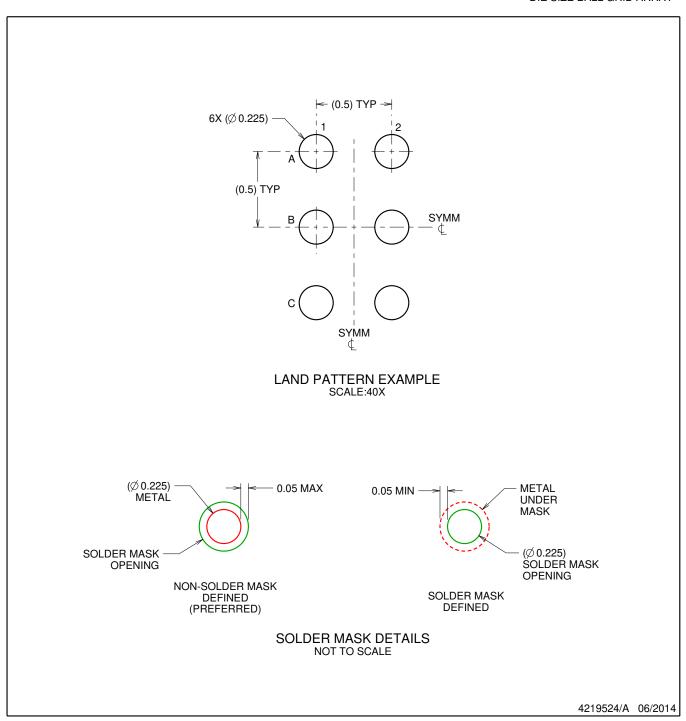
NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.
- 3. NanoFree<sup>™</sup> package configuration.



DIE SIZE BALL GRID ARRAY

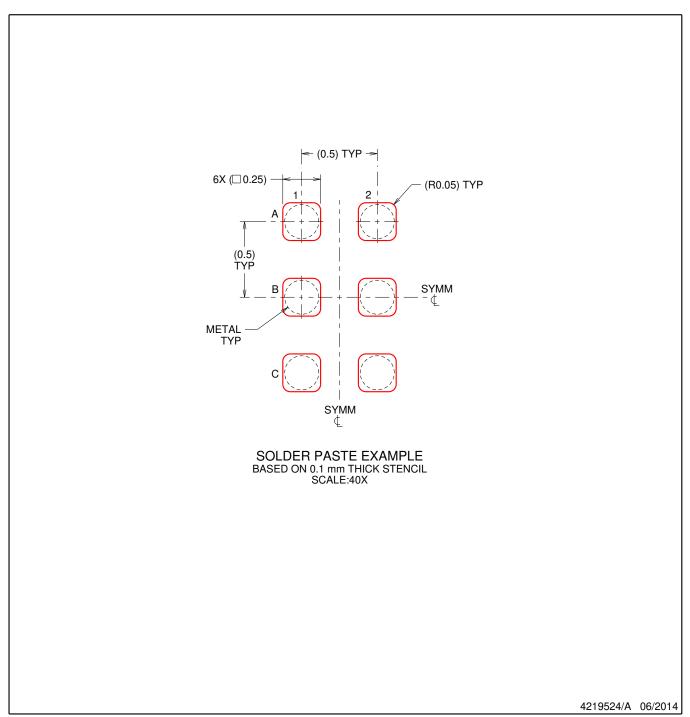


NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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